74LVC1G123-Q100

Single retriggerable monostable multivibrator; Schmitt trigger inputs

Rev. 1 — 10 March 2014

Product data sheet

1. General description

The 74LVC1G123-Q100 is a single retriggerable monostable multivibrator with Schmitt trigger inputs. Output pulse width is controlled by three methods:

- 1. The basic pulse is programmed by selection of an external resistor (R_{EXT}) and capacitor (C_{EXT}).
- 2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input (A) or the active HIGH-going edge input (B). By repeating this process, the output pulse period (Q = HIGH) can be made as long as desired. Alternatively an output delay can be terminated at any time by a LOW-going edge on input CLR, which also inhibits the triggering.
- 3. An internal connection from CLR to the input gates makes it possible to trigger the circuit by a HIGH-going signal at input CLR.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment. Schmitt trigger inputs, makes the circuit highly tolerant to slower input rise and fall times.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100 % duty factor
- Direct reset terminates output pulse
- Schmitt trigger on all inputs



- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- Power-on-reset on outputs
- Latch-up performance exceeds 100 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - ♦ HBM JESD22-A114F exceeds 2000 V
 - \bullet MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	mber Package						
	Temperature range	Name	Description	Version			
74LVC1G123DP-Q100	–40 °C to +125 °C		plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2			
74LVC1G123DC-Q100	–40 °C to +125 °C		plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1			

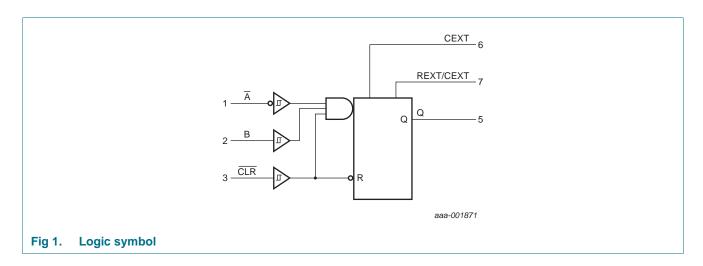
4. Marking

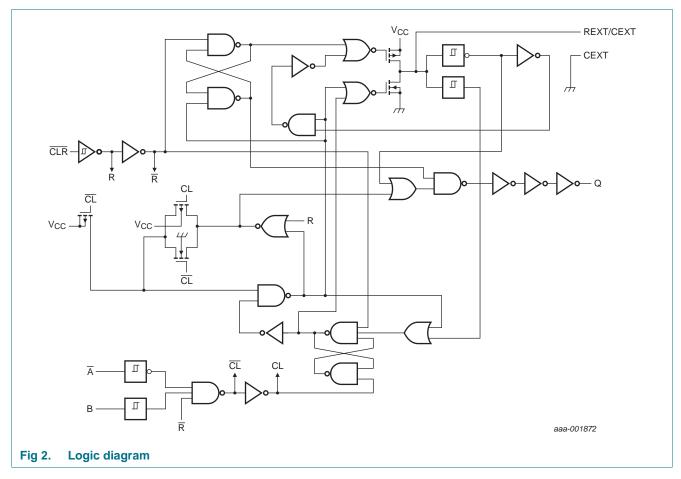
Table 2. Marking codes

Type number	Marking code ^[1]
74LVC1G123DP-Q100	Y3
74LVC1G123DC-Q100	Y3

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

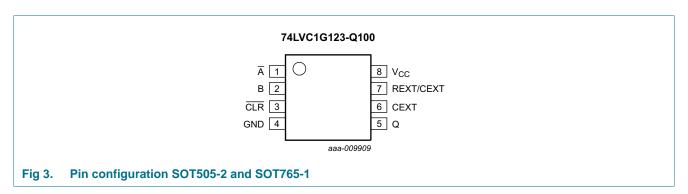
5. Functional diagram





6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
Ā	1	negative-edge triggered input
В	2	positive-edge triggered input
CLR	3	direct reset LOW and positive-edge triggered input
GND	4	ground (0 V)
Q	5	active HIGH output
CEXT	6	external capacitor connection
REXT/CEXT	7	external resistor and capacitor connection
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table[1]

Input			Output
CLR	Ā	В	Q
L	X	X	L
X	Н	X	<u>[2]</u>
X	X	L	<u>[2]</u>
Н	L	\uparrow	Л
Н	\	Н	Л
\uparrow	L	Н	Л

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = LOW-to-HIGH transition; ↓ = HIGH-to-LOW transition;

= one HIGH-level output pulse; = one LOW-level output pulse.

[2] If the monostable was triggered before this condition was established, the pulse continues as programmed.

74LVC1G123_Q100

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+6.5	V
VI	input voltage	[1]	-0.5	+6.5	V
Vo	output voltage	Active mode [1]	-0.5	V _{CC} + 0.5	V
		Power-down mode [1][2]	-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	$V_O < 0 \text{ V or } V_O > V_{CC}$	-	±50	mA
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	supply current		-	100	mA
I _{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	-	300	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- [2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.
- [3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 1.65 V to 5.5 V	-	1	ms/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C[1					
V _{OH}	HIGH-level	$V_I = V_{T+}$ or V_{T-}				
	output voltage	$I_{O} = -100 \mu A$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	V _{CC} - 0.1	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	V
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.4	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	V
V _{OL}	LOW-level	$V_I = V_{T+}$ or V_{T-}				
	output voltage	$I_O = 100 \mu A; V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V
		I _O = 8 mA; V _{CC} = 2.3 V	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	V
		I _O = 24 mA; V _{CC} = 3.0 V	-	-	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
II	input leakage current	$V_I = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±2	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	-	±2	μΑ
I _{CC}	supply current	V _I = 5.5 V or GND				
		Quiescent; $V_{CC} = 1.65 \text{ V}$ to 5.5 V; $I_{O} = 0 \text{ A}$	-	0.1	10	μΑ
		Active state; REXT/CEXT = 0.5V _{CC}				
		V _{CC} = 1.65 V	-	-	80	μΑ
		V _{CC} = 2.3 V	-	-	130	μΑ
		V _{CC} = 3 V	-	-	240	μΑ
		V _{CC} = 4.5 V	-	-	400	μΑ
		V _{CC} = 5.5 V	-	-	650	μΑ
Cı	input capacitance		-	2.0	-	pF

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +125 °C					
V _{OH}	HIGH-level	$V_I = V_{T+}$ or V_{T-}				
	output voltage	$I_{O} = -100 \mu A$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	V _{CC} - 0.1	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.4	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	V
V _{OL}	LOW-level	$V_I = V_{T+}$ or V_{T-}				
	output voltage	$I_O = 100 \mu A$; $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	0.1	V
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.3	V
		I _O = 12 mA; V _{CC} = 2.7 V	-	-	0.4	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
l _l	input leakage current	$V_I = 5.5 \text{ V or GND}; V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±10	μΑ
I _{OFF}	power-off leakage current	V_{I} or $V_{O} = 5.5 \text{ V}$; $V_{CC} = 0 \text{ V}$	-	-	±10	μА
I _{CC}	supply current	V _I = 5.5 V or GND				
		Quiescent; V _{CC} = 1.65 V to 5.5 V; I _O = 0 A	-	-	20	μА
		Active state; REXT/CEXT = 0.5V _{CC}				
		V _{CC} = 1.65 V	-	-	80	μА
		V _{CC} = 2.3 V	-	-	130	μА
		V _{CC} = 3 V	-	-	240	μА
		V _{CC} = 4.5 V	-	-	400	μΑ
		V _{CC} = 5.5 V	-	-	650	μΑ

^[1] All typical values are measured at T_{amb} = 25 °C.

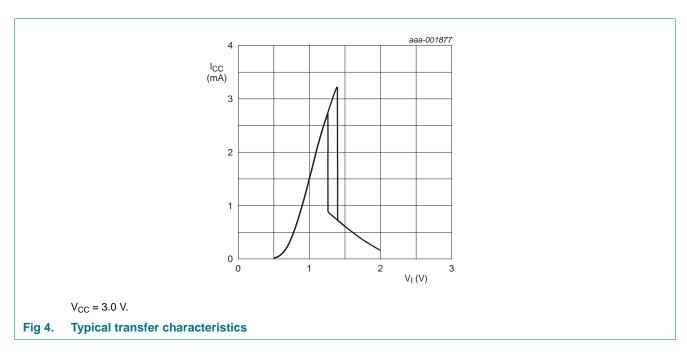
Table 8. Transfer characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 16.

Symbol	Parameter	Conditions	-4	0 °C to +8	5 °C	-40 °C	to +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
V _{T+}	positive-going threshold voltage	A, B and CLR input; see Figure 4						
		V _{CC} = 1.65 V to 1.95 V	0.72	0.98	1.22	0.71	1.22	V
		V _{CC} = 2.3 V to 2.7 V	0.97	1.26	1.52	0.97	1.52	V
		V _{CC} = 3.0 V to 3.6 V	1.20	1.58	1.90	1.20	1.90	V
		V _{CC} = 4.5 V to 5.5 V	1.74	2.27	2.75	1.74	2.78	V
V_{T-}	negative-going threshold voltage	A, B and CLR input; see Figure 4						
		V _{CC} = 1.65 V to 1.95 V	0.56	0.81	1.04	0.56	1.04	V
		V _{CC} = 2.3 V to 2.7 V	0.83	1.09	1.33	0.82	1.33	V
		V _{CC} = 3.0 V to 3.6 V	1.08	1.40	1.70	1.08	1.72	V
		V _{CC} = 4.5 V to 5.5 V	1.61	2.07	2.53	1.61	2.57	V
V _H	hysteresis voltage	\overline{A} , B and \overline{CLR} input; ($V_{T+} - V_{T-}$); see Figure 4						
		V _{CC} = 1.65 V to 1.95 V	61	170	295	54	295	mV
		V _{CC} = 2.3 V to 2.7 V	41	174	304	41	304	mV
		V _{CC} = 3.0 V to 3.6 V	40	183	319	40	319	mV
		V _{CC} = 4.5 V to 5.5 V	32	199	363	26	363	mV

^[1] All typical values are measured at $T_{amb} = 25$ °C.

10.1 Waveform transfer characteristics



11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 16.

Symbol	Parameter	Conditions		°C to +8	85 °C	-40 °C t	Unit	
			Min	Typ[1]	Max	Min	Max	
t _{pd}	propagation	A, B to Q; see Figure 5						
	delay	C _L = 15 pF						
		V _{CC} = 1.65 V to 1.95 V	2.5	7.1	16.3	2.5	17.6	ns
		V _{CC} = 2.3 V to 2.7 V	1.9	-	10.3	1.9	11.2	ns
		V _{CC} = 2.7 V	1.9	-	8.5	1.9	9.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	-	7.6	1.5	8.3	ns
		V _{CC} = 4.5 V to 5.5 V	1.2	-	5.3	1.2	5.8	ns
		$C_L = 30 \text{ pF or } C_L = 50 \text{ pF}$						
		V _{CC} = 1.65 V to 1.95 V	2.9	7.8	17.6	2.9	19.0	ns
		V _{CC} = 2.3 V to 2.7 V	2.2	-	11.3	2.2	12.3	ns
		V _{CC} = 2.7 V	2.7	-	10.5	2.7	11.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	-	9.5	2.0	10.3	ns
		V _{CC} = 4.5 V to 5.5 V	1.5	-	6.7	1.5	7.2	ns
		CLR to Q; see Figure 5						
		C _L = 15 pF						
		V _{CC} = 1.65 V to 1.95 V	3.0	6.9	16.2	3.0	17.4	ns
		V _{CC} = 2.3 V to 2.7 V	2.2	-	9.6	2.2	10.5	ns
		V _{CC} = 2.7 V	2.2	-	8.2	2.2	8.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	-	7.3	2.0	8.0	ns
		V _{CC} = 4.5 V to 5.5 V	1.5	-	5.1	1.5	5.5	ns
		$C_L = 30 \text{ pF or } C_L = 50 \text{ pF}$						
		V _{CC} = 1.65 V to 1.95 V	3.3	7.5	17.2	3.8	18.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.5	-	10.3	2.0	11.2	ns
		V _{CC} = 2.7 V	2.8	-	9.3	2.8	10.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	-	8.4	1.5	9.2	ns
		V _{CC} = 4.5 V to 5.5 V	1.5	-	6.0	1.5	6.6	ns

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 16.

Symbol	Parameter	Conditions	-40	°C to +8	85 °C	-40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
t _{pd}	t _{pd} propagation	CLR to Q (trigger); see Figure 5						
	delay	C _L = 15 pF						
		V _{CC} = 1.65 V to 1.95 V	2.7	7.6	17.4	2.7	18.9	ns
		V _{CC} = 2.3 V to 2.7 V	2.1	-	11.0	2.1	12.0	ns
		V _{CC} = 2.7 V	2.1	-	9.2	2.1	10.0	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	-	8.2	1.7	8.9	ns
		V _{CC} = 4.5 V to 5.5 V	1.4	-	5.9	1.4	6.4	ns
		$C_L = 30 \text{ pF or } C_L = 50 \text{ pF}$						
		V _{CC} = 1.65 V to 1.95 V	3.1	8.3	18.8	3.3	20.3	ns
		V _{CC} = 2.3 V to 2.7 V	2.5	-	12.0	2.5	13.1	ns
		V _{CC} = 2.7 V	2.8	-	11.1	2.8	12.1	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	-	10.1	2.0	11.0	ns
		V _{CC} = 4.5 V to 5.5 V	1.5	-	7.1	1.5	7.7	ns
t _W	pulse width	input A LOW; B HIGH; see Figure 5 and Figure 6						
		V _{CC} = 1.65 V to 1.95 V	8.0	-	-	8.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	4.0	-	-	4.0	-	ns
		V _{CC} = 2.7 V	3.0	-	-	3.0	-	ns
		V _{CC} = 3.0 V to 3.6 V	3.0	-	-	3.0	-	ns
		V _{CC} = 4.5 V to 5.5 V	2.5	-	-	2.5	-	ns
		input CLR LOW; see Figure 5 and Figure 7						
		V _{CC} = 1.65 V to 1.95 V	8.0	-	-	8.0	-	ns
		V _{CC} = 2.3 V to 2.7 V	4.0	-	-	4.0	-	ns
		V _{CC} = 2.7 V	3.0	-	-	3.0	-	ns
		V _{CC} = 3.0 V to 3.6 V	3.0	-	-	3.0	-	ns
		V _{CC} = 4.5 V to 5.5 V	2.5	-	-	2.5	-	ns

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 16.

Symbol	Parameter	Conditions	-40	°C to +8	5°C	5 °C -40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t _W	pulse width	output Q HIGH; see Figure 5, Figure 6 and Figure 7; $R_{EXT} = 10 \text{ k}\Omega$	3]					
		C _{EXT} = 100 pF						
		V _{CC} = 1.65 V to 1.95 V	-	1.4	2.2	-	2.2	μS
		V _{CC} = 2.3 V to 2.7 V	-	1.3	1.8	-	1.8	μS
		V _{CC} = 2.7 V	-	1.2	1.8	-	1.8	μS
		V _{CC} = 3.0 V to 3.6 V	-	1.2	1.8	-	1.8	μS
		V _{CC} = 4.5 V to 5.5 V	-	1.2	1.8	-	1.8	μS
			3]					
		V _{CC} = 1.65 V to 1.95 V	-	100	110	-	110	μS
		V _{CC} = 2.3 V to 2.7 V	-	100	110	-	110	μS
		V _{CC} = 2.7 V	-	100	110	-	110	μS
		V _{CC} = 3.0 V to 3.6 V	-	100	110	-	110	μS
		V _{CC} = 4.5 V to 5.5 V	-	100	110	-	110	μS
		$C_{EXT} = 0.1 \mu F$	3]					
		V _{CC} = 1.65 V to 1.95 V	-	1.0	1.05	-	1.05	ms
		V _{CC} = 2.7 V	-	1.0	1.05	-	1.05	ms
		V _{CC} = 3.0 V to 3.6 V	-	1.0	1.05	-	1.05	ms
		V _{CC} = 3.0 V to 3.6 V	-	1.0	1.05	-	1.05	ms
		V _{CC} = 4.5 V to 5.5 V	-	1.0	1.05	-	1.05	ms
t _{rtrig}	retrigger time	A, B; see Figure 6						
		$C_{EXT} = 100 \text{ pF}; R_{EXT} = 5 \text{ k}\Omega$						
		V _{CC} = 1.65 V to 1.95 V	-	174	-	-	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	59	-	-	-	ns
		$C_{EXT} = 100 \text{ pF}; R_{EXT} = 1 \text{ k}\Omega$						
		V _{CC} = 3.0 V to 3.6 V	-	32	-	-	-	ns
		V _{CC} = 4.5 V to 5.5 V	-	20	-	-	-	ns
		$C_{EXT} = 100 \mu F; R_{EXT} = 5 k\Omega$						
		V _{CC} = 1.65 V to 1.95 V	-	14	-	-	-	ms
		V _{CC} = 2.3 V to 2.7 V	-	10	-	-	-	ms
		$C_{EXT} = 100 \mu F; R_{EXT} = 1 k\Omega$						
		V _{CC} = 3.0 V to 3.6 V	-	10	-	-	-	ms
		V _{CC} = 4.5 V to 5.5 V	-	8	-	-	-	ms
R _{ext}	external	see Figure 10, Figure 11 and Figure 12						
	resistance	V _{CC} = 2.0 V	5	-	-	-	-	kΩ
		V _{CC} ≥ 3.0 V	1	-	-	-	-	kΩ
C _{ext}	external capacitance	V _{CC} = 5.0 V; see <u>Figure 10</u> , <u>Figure 11</u> and <u>Figure 12</u>	-	-	-	-	-	pF

 Table 9.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 16.

Symbol	Parameter	Conditions	-40	°C to +8	5 °C	-40 °C to	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
C _{PD} power dissipation capacitance		$V_I = GND$ to V_{CC} ; $C_{EXT} = 0$ pF						
	$R_{EXT} = 5 \text{ k}\Omega$							
	Capacitarice	V _{CC} = 1.8 V	-	35	-	-	-	pF
	V _{CC} = 2.5 V	-	35	-	-	-	pF	
		$R_{EXT} = 1 \text{ k}\Omega$						
		V _{CC} = 3.3 V	-	27	-	-	-	pF
		V _{CC} = 5.0 V	-	29	-	-	-	pF

- [1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 3.3 V and 5.0 V respectively.
- [2] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [3] For other R_{EXT} and C_{EXT} combinations see Figure 10, Figure 11 and Figure 12. If C_{EXT} > 10 nF, the next formula is valid.

 t_W = K \times R_{EXT} \times C_{EXT}, where:

 t_W = typical output pulse width in ns;

 R_{EXT} = external resistor in $k\Omega$;

C_{EXT} = external capacitor in pF;

K = constant = 1; see Figure 13 for typical "K" factor as function of V_{CC} .

12. Waveforms, graphs and test circuit

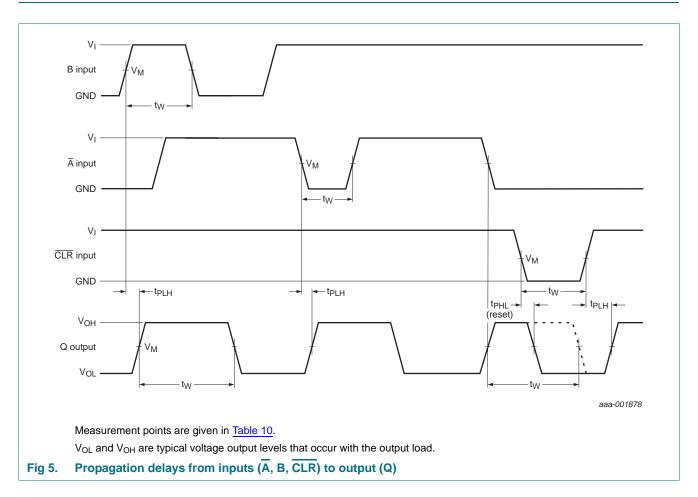
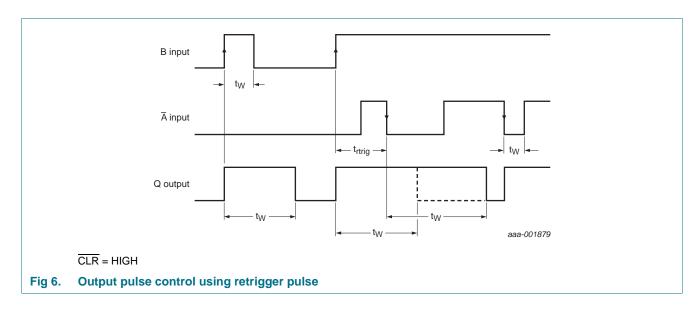
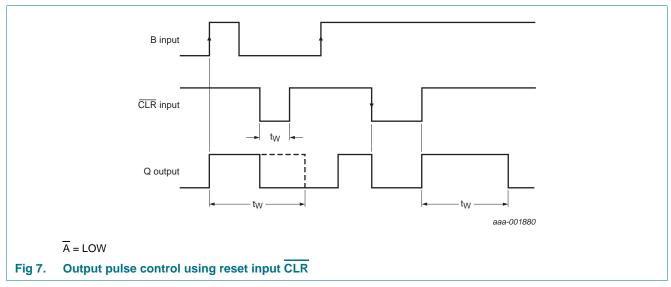
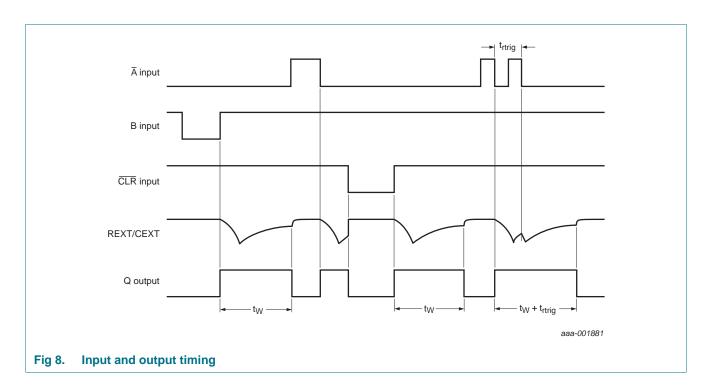


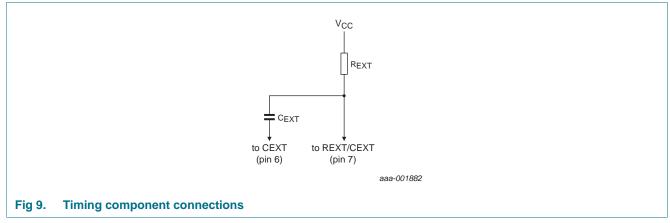
Table 10. Measurement points

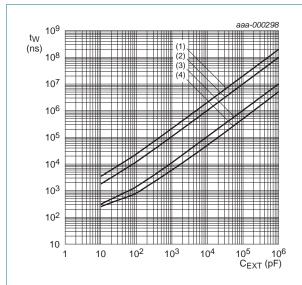
Supply voltage	Input	Output
V _{CC}	V _M	V _M
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}







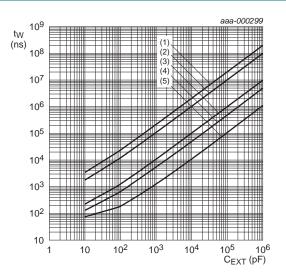




$$V_{CC}$$
 = 1.8 V; T_{amb} = 25 °C.

- (1) $R_{EXT} = 200 \text{ k}\Omega$
- (2) $R_{EXT} = 100 \text{ k}\Omega$
- (3) $R_{EXT} = 10 \text{ k}\Omega$
- (4) $R_{EXT} = 5 k\Omega$

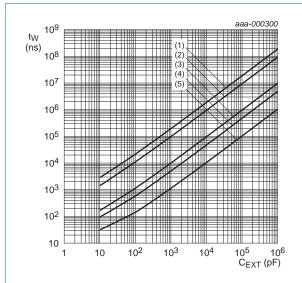
Fig 10. Typical output pulse width as a function of the external capacitor value



$$V_{CC} = 3.3 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}.$$

- (1) $R_{EXT} = 200 \text{ k}\Omega$
- (2) $R_{EXT} = 100 kΩ$
- (3) $R_{EXT} = 10 \text{ k}\Omega$
- (4) $R_{EXT} = 5 k\Omega$
- (5) $R_{EXT} = 1 k\Omega$

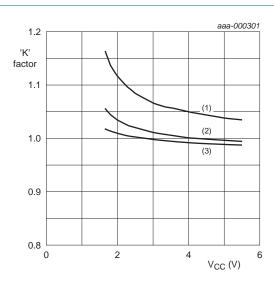
Fig 11. Typical output pulse width as a function of the external capacitor value



 V_{CC} = 5.0 V; T_{amb} = 25 °C.

- (1) $R_{EXT} = 200 \text{ k}\Omega$
- (2) $R_{EXT} = 100 \text{ k}\Omega$
- (3) $R_{EXT} = 10 \text{ k}\Omega$
- (4) $R_{EXT} = 5 k\Omega$
- (5) $R_{EXT} = 1 k\Omega$

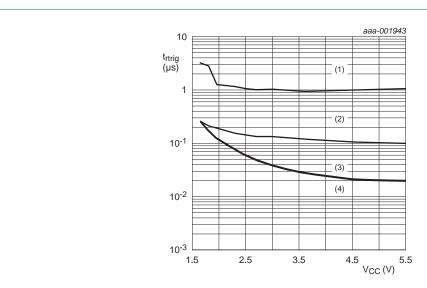
Fig 12. Typical output pulse width as a function of the external capacitor value



 R_{EXT} = 10 k Ω ; T_{amb} = 25 °C.

- (1) $C_{EXT} = 1000 pF$
- (2) $C_{EXT} = 0.01 \mu F$
- (3) $C_{EXT} = 0.1 \mu F$

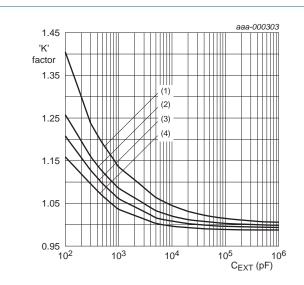
Fig 13. Typical 'K' factor as function of V_{CC}



 $T_{amb} = 25 \, ^{\circ}C.$

- (1) $C_{EXT} = 0.01 \mu F$
- (2) $C_{EXT} = 1000 pF$
- (3) $C_{EXT} = 100 pF$
- (4) $C_{EXT} = 10 pF$

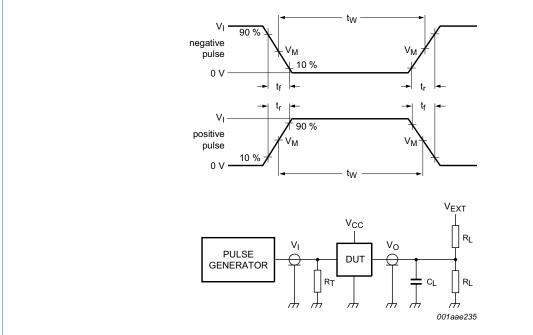
Fig 14. Minimum retrigger time as function of the supply voltage



 R_{EXT} = 10 k Ω ; T_{amb} = 25 °C.

- (1) $V_{CC} = 1.8 \text{ V}$
- (2) $V_{CC} = 2.5 \text{ V}$
- (3) $V_{CC} = 3.3 \text{ V}$
- (4) $V_{CC} = 5.0 \text{ V}$

Fig 15. Typical 'K' factor as function of CEXT



Test data is given in Table 11.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

V_{EXT} = Test voltage for switching times.

Fig 16. Test circuit for measuring switching times

Table 11. Test data

Supply voltage	Input		Load	V _{EXT}	
V _{cc}	V _I	t _r , t _f	C _L	R _L	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	15 pF	1 ΜΩ	open
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	15 pF	1 ΜΩ	open
2.7 V	2.7 V	≤ 2.5 ns	15 pF	1 ΜΩ	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	15 pF	1 ΜΩ	open
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	15 pF	1 ΜΩ	open
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V _{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	500 Ω	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

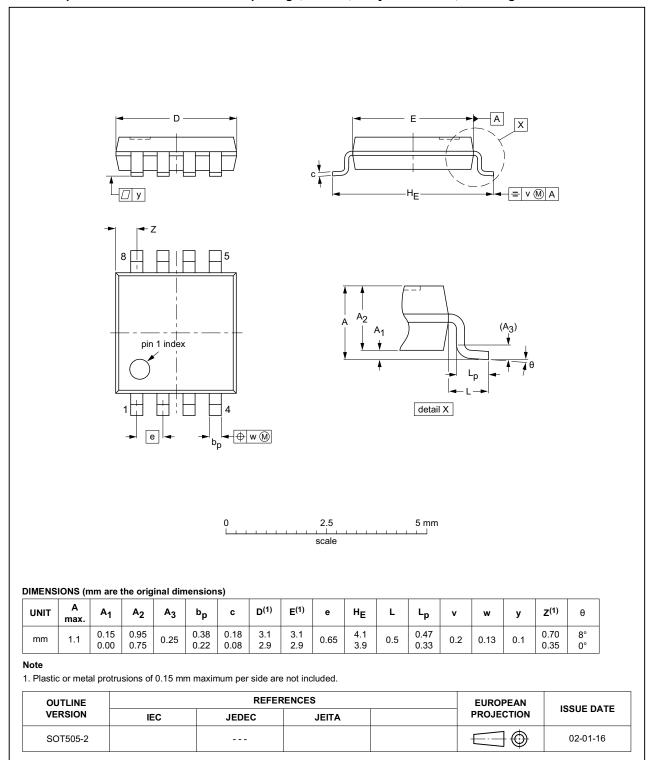


Fig 17. Package outline SOT505-2 (TSSOP8)

74LVC1G123_Q100

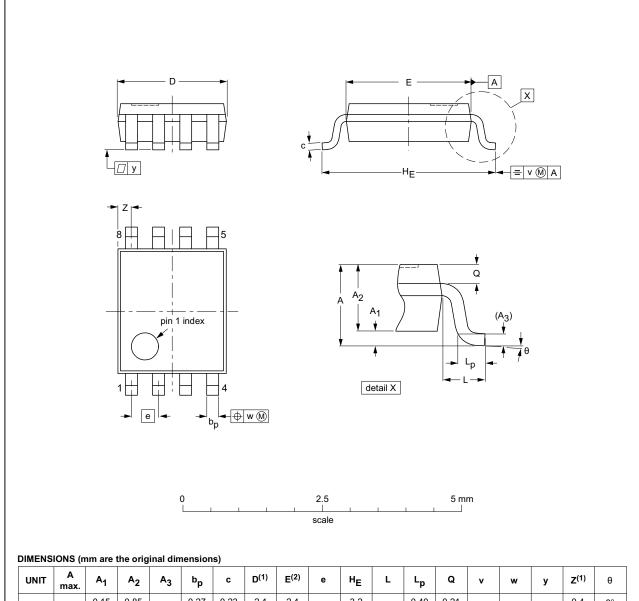
Product data sheet

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VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	ď	>	¥	у	Z ⁽¹⁾	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT765-1		MO-187			02-06-07	

Fig 18. Package outline SOT765-1 (VSSOP8)

74LVC1G123_Q100

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14. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MIL	Military
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G123_Q100 v.1	20140310	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Single retriggerable monostable multivibrator; Schmitt trigger inputs

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